

Features

- For surface mount applications
- Glass passivated chip junction
- Low profile package
- Easy to pick and place

SMBF



1.Cathode  2.Anode

Marking Code:

S3ABF-TN: S3AB
S3BBF-TN: S3BB
S3DBF-TN: S3DB
S3GBF-TN: S3GB
S3JBF-TN: S3JB
S3KBF-TN: S3KB
S3MBF-TN: S3MB

Maximum Ratings and Electrical Characteristics

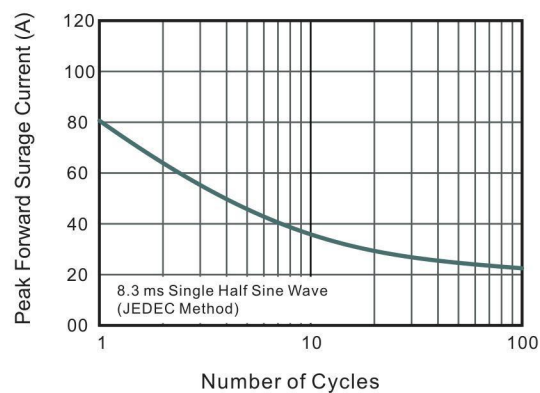
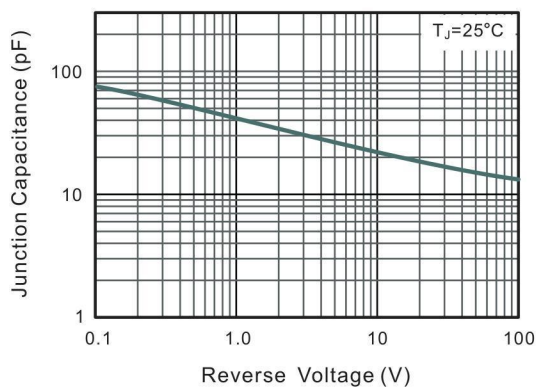
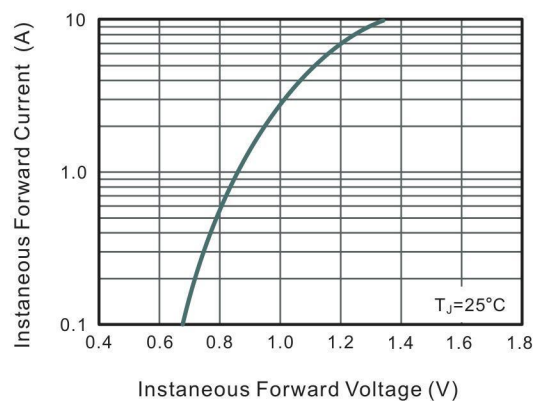
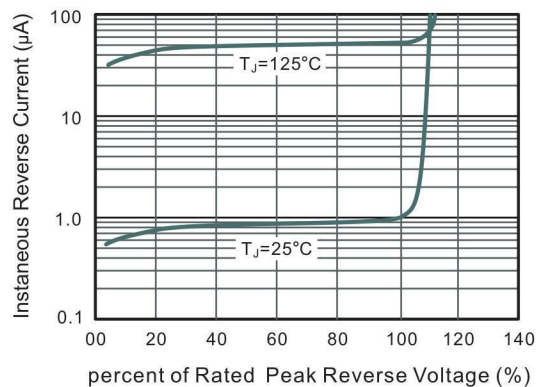
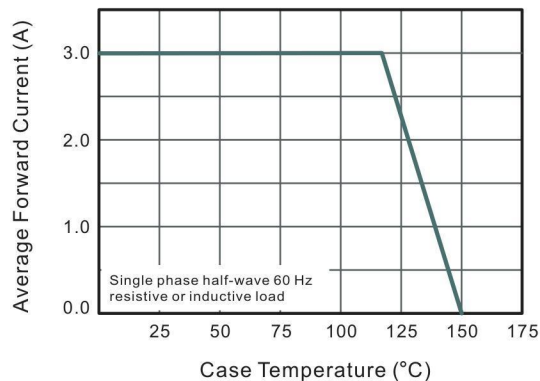
Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	S3ABF-TN	S3BBF-TN	S3DBF-TN	S3GBF-TN	S3JBF-TN	S3KBF-TN	S3MBF-TN	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_C = 115^\circ\text{C}$	$I_{F(AV)}$	3.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	80							A
Maximum Instantaneous Forward Voltage at 3 A	V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	I_R	5 150							μA
Typical Junction Capacitance ^{Note1}	C_j	35							pF
Typical Thermal Resistance ^{Note2}	$R_{\theta JA}$ $R_{\theta JC}$	45 15							$^\circ\text{C/W}$
Junction Temperature	T_J	150							$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150							$^\circ\text{C}$

Note:

1. Measured at 1 MHz and applied reverse voltage of 4 V D.C
2. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

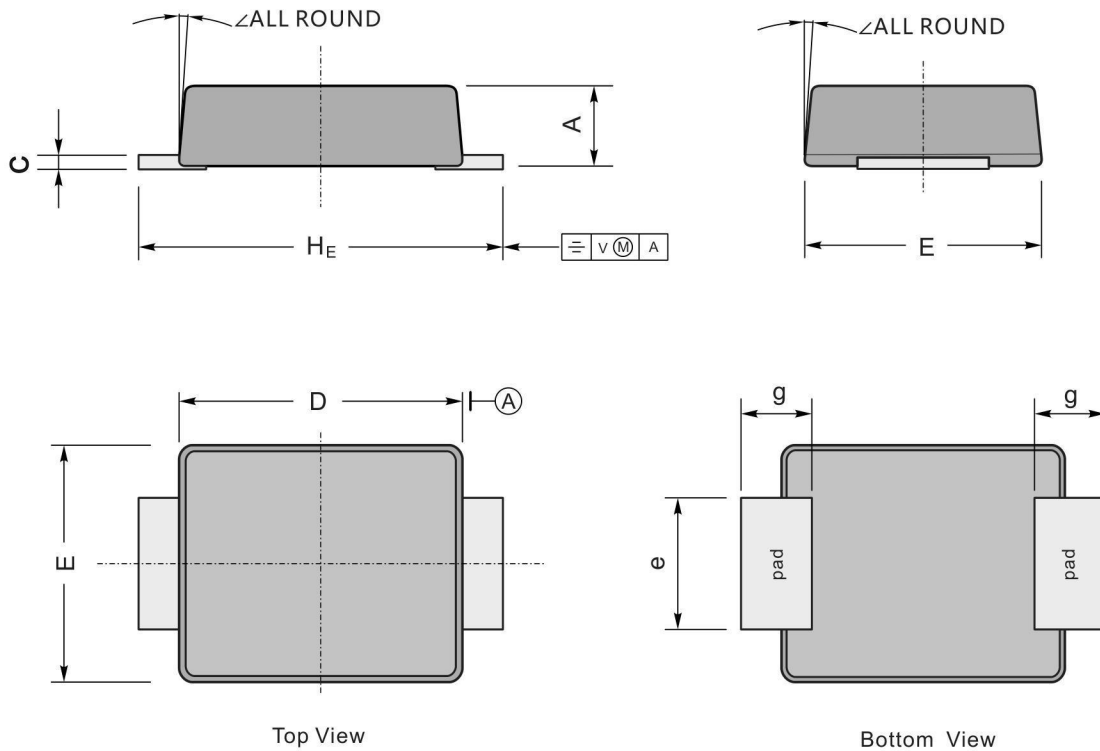
Typical Characteristic Curves



Package Outline

SMBF

Dimensions in mm



UNIT		A	C	D	E	H _E	e	g	∠
mm	max	1.3	0.26	4.4	3.7	5.5	2.2	1.0	9°
	min	1.1	0.18	4.2	3.5	5.1	1.9		
mil	max	51	10	173	146	216	86	40	
	min	43	7	165	138	200	75		